

# Usha C

## List of Publications by Year in descending order

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11  
papers

57  
citations

2258059

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h-index

1872680

6  
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12  
all docs

12  
docs citations

12  
times ranked

23  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Analytical Drain Current Model for Fully Depleted Surrounding Gate TFET. Journal of Nano Research, 0, 55, 75-81.   | 0.8 | 13        |
| 2  | A novel 2-D analytical model for the electrical characteristics of a gate-all-around heterojunction tunnel field-effect transistor including depletion regions. Journal of Computational Electronics, 2020, 19, 1144-1153. | 2.5 | 11        |
| 3  | A new analytical approach to threshold voltage modeling of triple material gate-all-around heterojunction tunnel field effect transistor. Indian Journal of Physics, 2021, 95, 1365-1371.                                  | 1.8 | 8         |
| 4  | A tunneling FET exploiting in various structures and different models: A review. , 2015, , .   |     | 7         |
| 5  | Electrostatic characteristics of a high-k stacked gate-all-around heterojunction tunnel field-effect transistor using the superposition principle. Journal of Computational Electronics, 2022, 21, 181-190.                | 2.5 | 5         |
| 6  | An Analytical Modeling of Conical Gate-All-Around Tunnel Field Effect Transistor. Silicon, 2021, 13, 2563-2568.  | 3.3 | 4         |
| 7  | Analytical Drain Current Modeling and Simulation of Triple Material Gate-All-Around Heterojunction TFETs Considering Depletion Regions. Semiconductors, 2020, 54, 1634-1640.   | 0.5 | 3         |
| 8  | Modeling of Source Pocket Engineered PNP Tunnel FET on High-K Buried Oxide (H-BOX) Substrate for Improved ON Current. Silicon, 2022, 14, 10383-10389.  | 3.3 | 3         |
| 9  | A compact two-dimensional analytical model of the electrical characteristics of a triple-material double-gate tunneling FET structure. Journal of Semiconductors, 2019, 40, 122901.  | 3.7 | 1         |
| 10 | Physics based model for potential distribution and threshold voltage of gate-all-around tunnel field effect transistor (GAA-TFET). Materials Today: Proceedings, 2021, 45, 4052-4057.                                      | 1.8 | 1         |
| 11 | Impact Analysis and Simulation of Cylindrical Nanowire Biosensor. , 2021, , .  |     | 1         |